

**2Т3511 – NPN силициев планарно-эпитаксиален
маломощен транзистор – BG
корпус С65 (ТО-92)**

маса max – 0,4 g

група Б

- $U_{CB} \text{ max} = 20 \text{ V}$
- $U_{EB} \text{ max} = 5 \text{ V}$
- $U_{CE} \text{ max} = 18 \text{ V}$
- $I_C \text{ max} = 100 \text{ mA}$
- $P_C \text{ max} = 200 \text{ mW}$
- $f_t = 120 \text{ MHz (min)} - U_{CE} = 10 \text{ V}; I_C = 10 \text{ mA}; f = 100 \text{ MHz}$
- $C_{tc} = 6 \text{ pF (max)} - U_{CE} = 10 \text{ V}; I_E = 0 \text{ mA}; f = 1 \text{ MHz}$
- $h_{11e} = 4 \text{ k}\Omega$
- $h_{12e} = 1,1 \cdot 10^{-4}$
- $h_{21e} = \beta = 20 \text{ (min)} \div 200 \text{ (max)} - U_{CE} = 10 \text{ V}; I_E = 1 \text{ mA}; f = 1 \text{ kHz}$
- $h_{22e} = 14 \text{ }\mu\text{S}$
- $U_{(BR)CEO} = 18 \text{ V}; I_E = 100 \text{ }\mu\text{A}; I_C = 0 \text{ }\mu\text{A}$
- $I_{CBO} = 50 \text{ }\mu\text{A} - U_{CB} = 10 \text{ V}; I_E = 0 \text{ }\mu\text{A}$
- $I_{CBO} = 50 \text{ }\mu\text{A} - U_{CB} = 20 \text{ V}; I_E = 0 \text{ }\mu\text{A}$
- $I_{EBO} = 1 \text{ }\mu\text{A}$
- $I_{EBO} = 20 \text{ }\mu\text{A} - U_{EB} = 1 \text{ V}; I_C = 0 \text{ }\mu\text{A}$
- $I_{EBO} = 10 \text{ }\mu\text{A} - U_{EB} = 5 \text{ V}; I_C = 0 \text{ }\mu\text{A}$
- $t_j \text{ max} = 125 \text{ }^\circ\text{C}$
- $t_{stg} = -25 \text{ }^\circ\text{C} \div +100 \text{ }^\circ\text{C}$
- цокъл 7